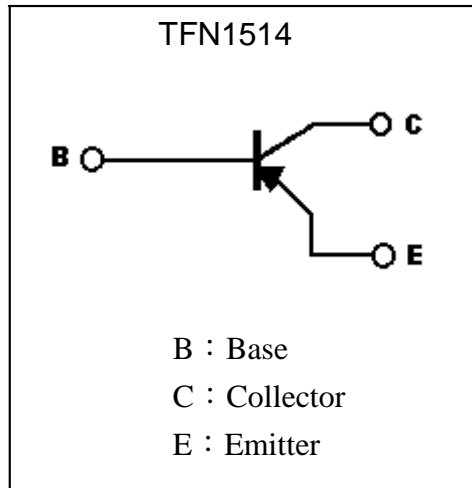


# TFN1514

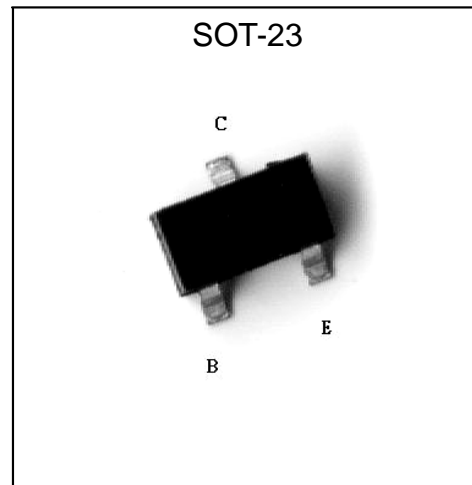
## Description

- The TFN1514 is designed for general purpose application requiring high breakdown voltage.
- Large  $I_C$  ,  $I_{C(Max)} = -0.6A$
- High  $BV_{CEO}$ ,  $BV_{CEO} = -150V$
- Complementary to TFN3906.
- Pb-free package

## Symbol



## Outline



## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CB0}$	-160	V
Collector-Emitter Voltage	$V_{CEO}$	-150	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-0.6	A
Power Dissipation	$P_d$	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~+150	°C



Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CB0</sub>	-160	-	-	V	I <sub>C</sub> =-50μA
BV <sub>CEO</sub>	-150	-	-	V	I <sub>C</sub> =-1mA
BV <sub>EBO</sub>	-5	-	-	V	I <sub>E</sub> =-50μA
I <sub>CB0</sub>	-	-	-50	nA	V <sub>CB</sub> =-120V
I <sub>EBO</sub>	-	-	-50	nA	V <sub>EB</sub> =-4V
*V <sub>CE(sat)</sub> 1	-	-	-0.2	V	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA
*V <sub>CE(sat)</sub> 2	-	-	-0.5	V	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA
*V <sub>BE(sat)</sub> 1	-	-	-1	V	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA
*V <sub>BE(sat)</sub> 2	-	-	-1	V	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA
h <sub>FE</sub> 1	50	-	-	-	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA
h <sub>FE</sub> 2	60	-	-	-	V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA
h <sub>FE</sub> 3	50	-	-	-	V <sub>CE</sub> =-5V, I <sub>C</sub> =-50mA
h <sub>FE</sub> 4	120	-	390	-	V <sub>CE</sub> =-6V, I <sub>C</sub> =-2mA
f <sub>T</sub>	100	-	-	MHz	V <sub>CE</sub> =-30V, I <sub>C</sub> =-10mA, f=100MHz
C <sub>ob</sub>	-	-	6	pF	V <sub>CB</sub> =-10V, f=1MHz

\*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

Classification Of h<sub>FE</sub> 4

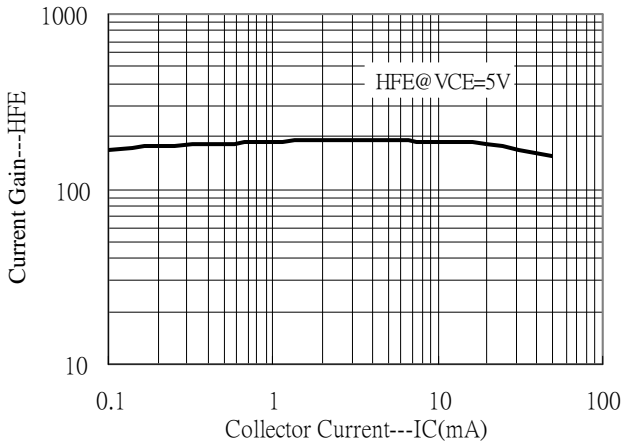
Rank	Q	R
Range	120~270	180~390

Ordering Information

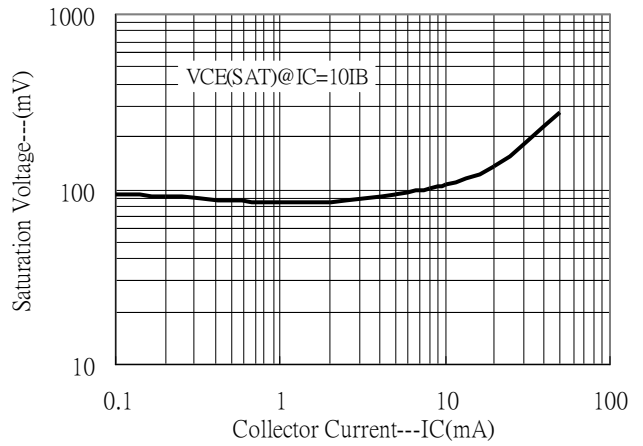
Device	Package	Shipping	Marking
TFN1514	SOT-23 (Pb-free)	3000 pcs / Tape & Reel	2L

Characteristic Curves

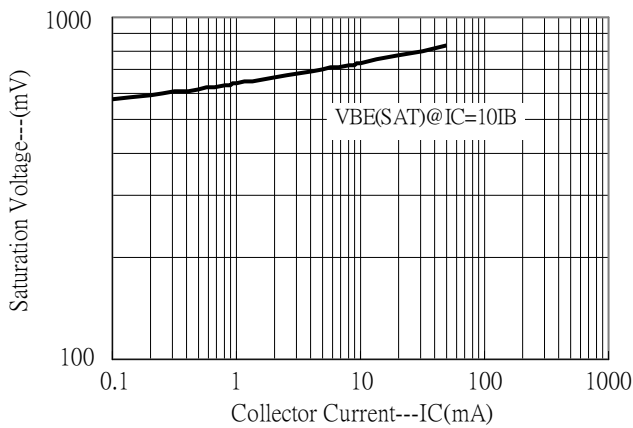
Current Gain vs Collector Current



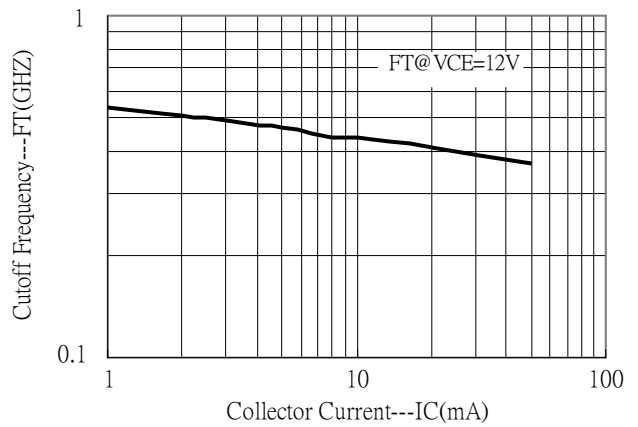
Saturation Voltage vs Collector Current



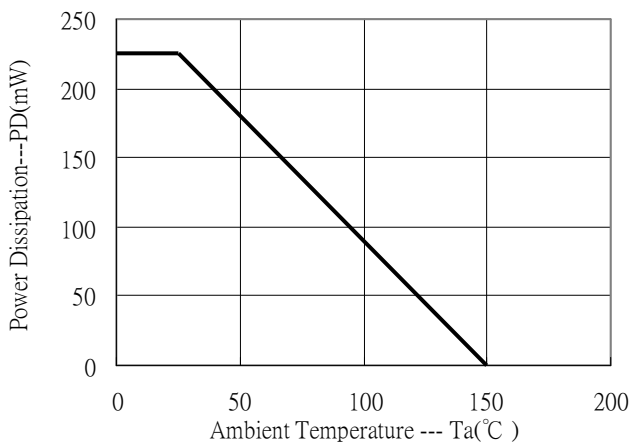
Saturation Voltage vs Collector Current



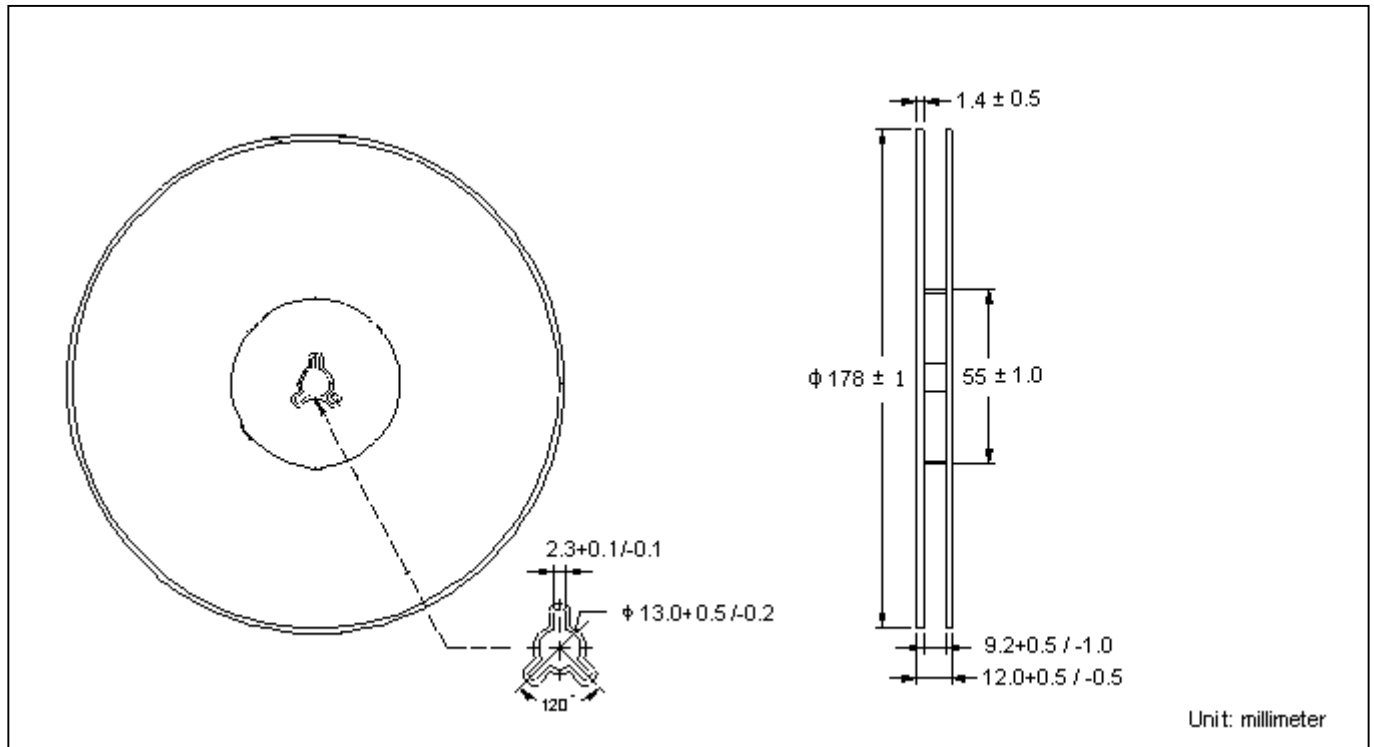
Cutoff Frequency vs Collector Current



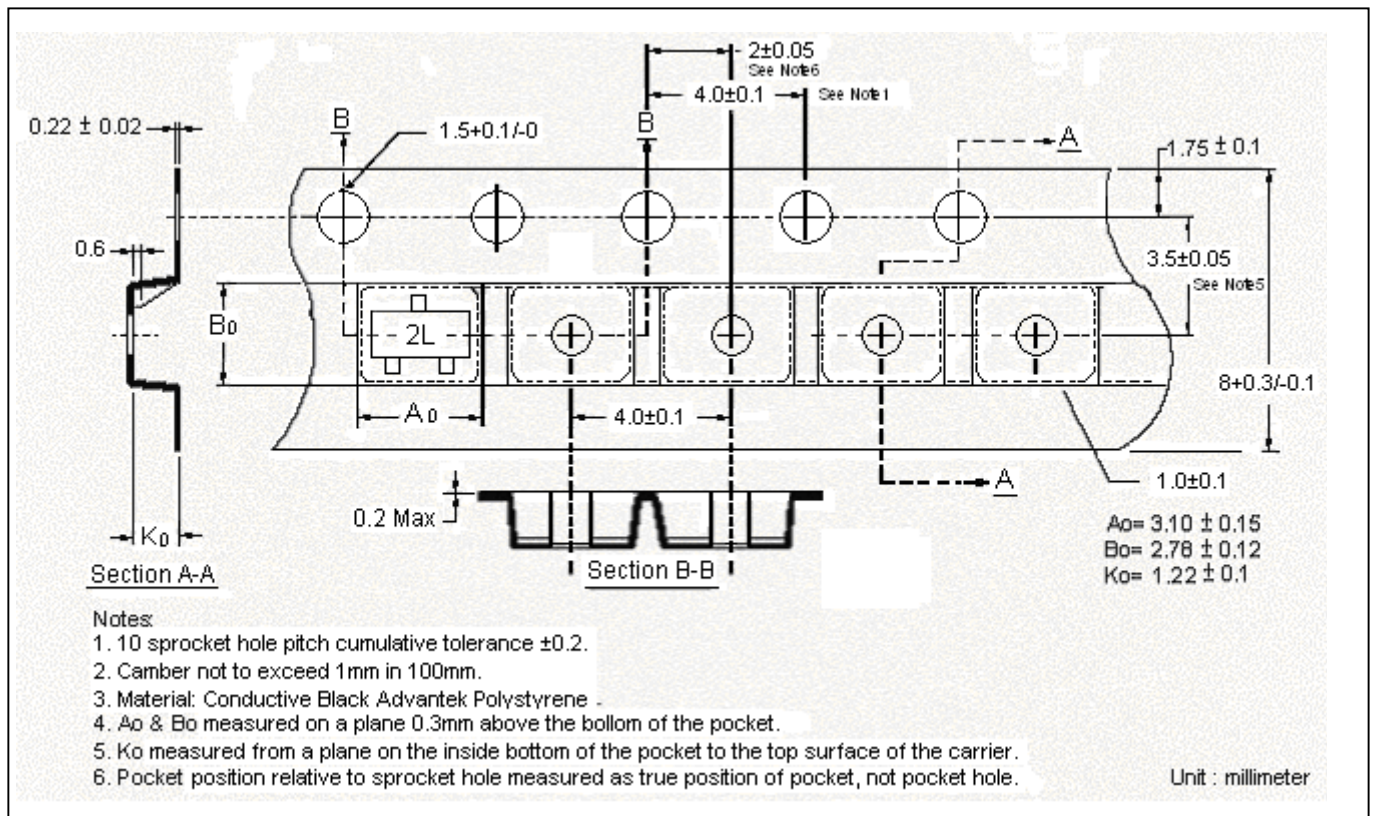
Power Derating Curve



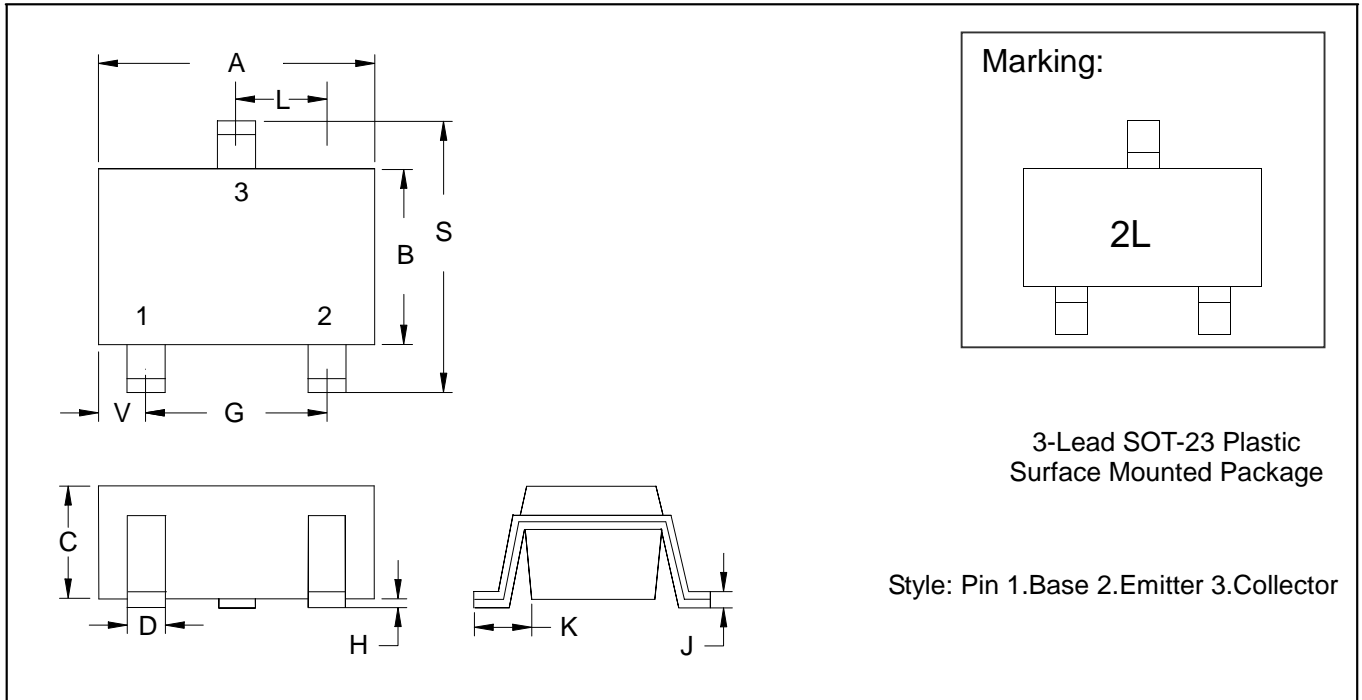
### Reel Dimension



### Carrier Tape Dimension



## SOT-23 Dimension



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1083	2.10	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local Tin Far sales office.

**Material:**

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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